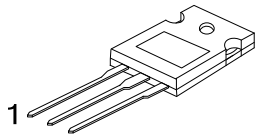
12N120-E4

Preliminary ***Power MOSFET***

12A, 1200V N-CHANNEL POWER MOSFET



TO-247

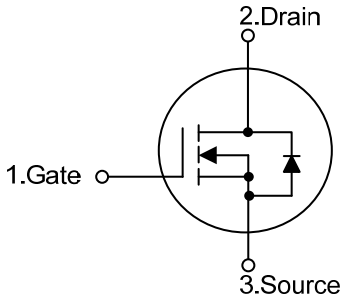
■ DESCRIPTION

The UTC **12N120-E4** provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

■ FEATURES0

* $R_{DS(ON)} \leq 1.8\ \Omega$ @ V_{GS}=10V, I_D=6.0A
* Low Reverse Transfer Capacitance
* Fast Switching Capability
* Avalanche Energy Specified
* Improved dv/dt Capability, High Ruggedness

■ SYMBOL



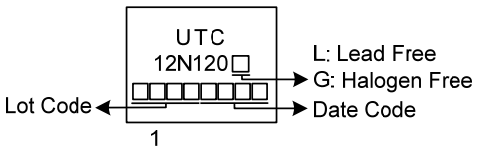
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
12N120L-T47-T	12N120G-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

12N120G-T47-T (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube (2) T47: TO-247 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	1200	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	12	A
	Pulsed (Note 2)	I_{DM}	24	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	108	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	1.1	V/ns
Power Dissipation		P_D	350	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L=30mH, I_{AS}=2.7A, V_{DD}=120V, R_G=25 Ω, Starting T_J = 25°C
4. I_{SD} ≤ 15A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

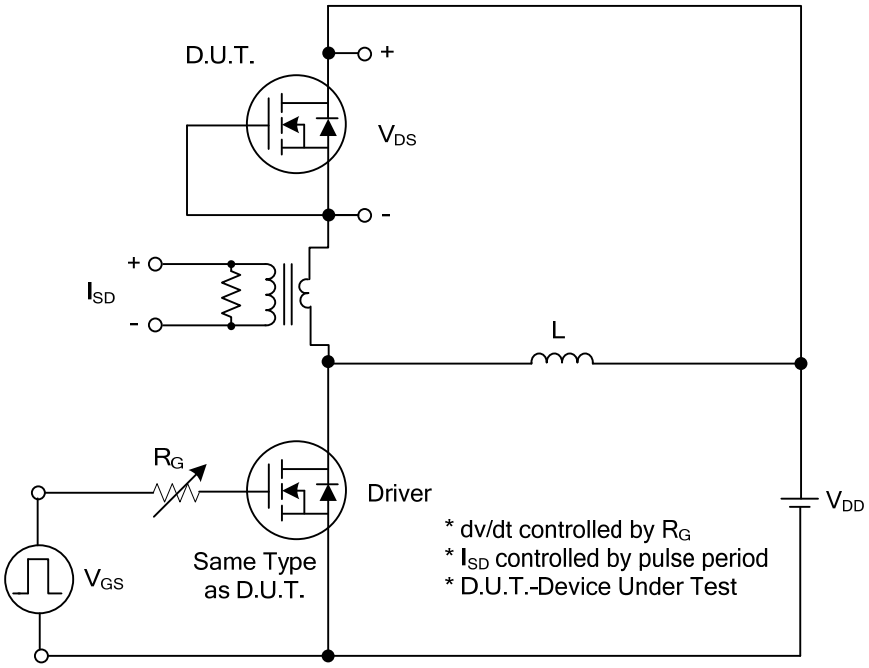
PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	50	°C/W
Junction to Case	θ_{JC}	0.35	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

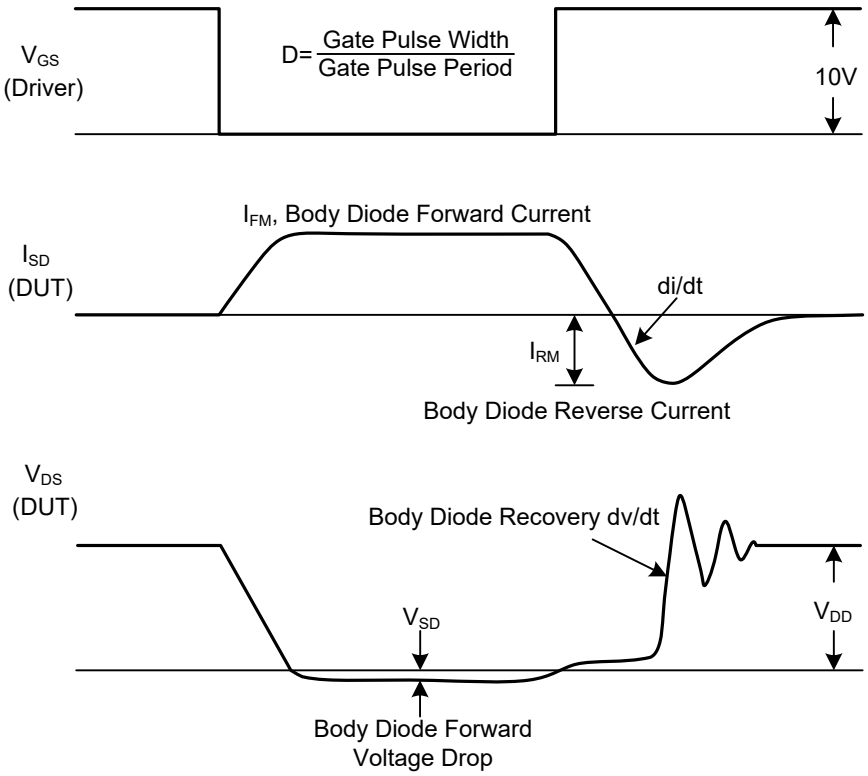
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	1200			V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=1200V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	3.0		5.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=6.0A			1.8	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	V_{DS}=25V, V_{GS}=0V, f=1MHz		2300		pF
Output Capacitance	C_{OSS}			245		pF
Reverse Transfer Capacitance	C_{RSS}			82		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	V_{DS}=960V, V_{GS}=10V, I_D=12A (Note 1, 2)		114		nC
Gate-Source Charge	Q_{GS}			28		nC
Gate-Drain Charge	Q_{GD}			56		nC
Turn-On Delay Time (Note 1)	$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D=12A, R_G =25Ω (Note 1, 2)		44		ns
Turn-On Rise Time	t_R			47		ns
Turn-Off Delay Time	$t_{D(OFF)}$			316		ns
Turn-Off Fall Time	t_F			108		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				12	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				24	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	I_S=12A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	I_S=12A, V_{GS}=0V, dI_F/dt=100A/μs		1200		nS
Body Diode Reverse Recovery Charge	Q_{rr}			24.6		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle≤2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

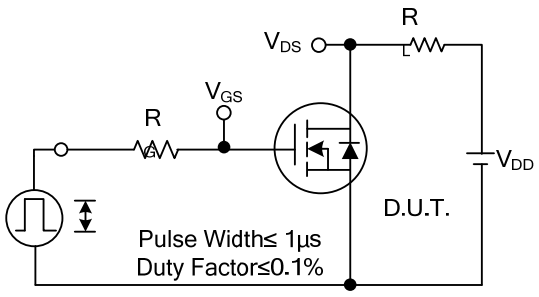


Peak Diode Recovery dv/dt Test Circuit

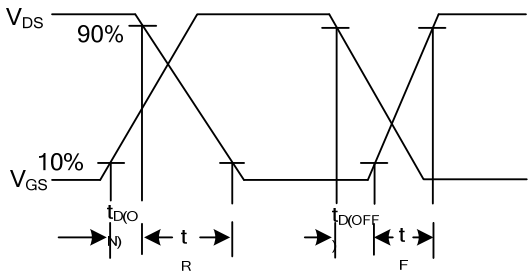


Peak Diode Recovery dv/dt Waveforms

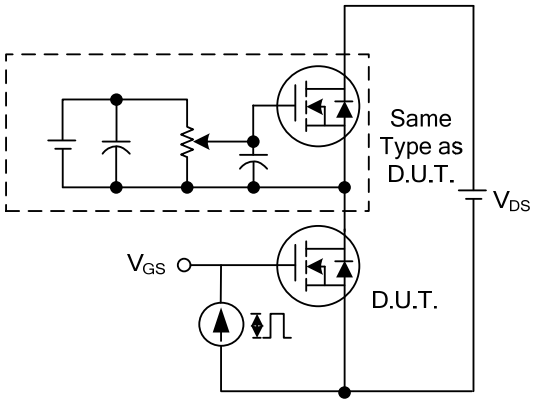
■ TEST CIRCUITS AND WAVEFORMS



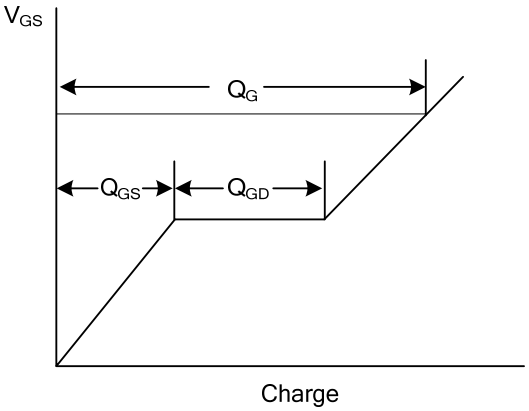
Switching Test Circuit



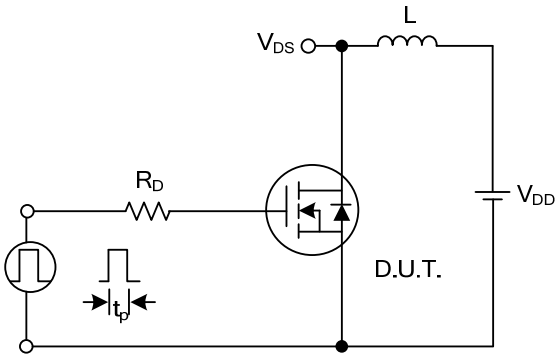
Switching Waveforms



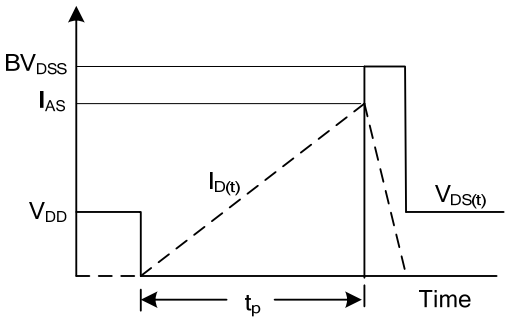
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms